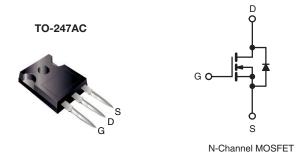
Vishay Siliconix

HALOGEN

FREE

## **D Series Power MOSFET**

PRODUCT SUMMARY			
V <sub>DS</sub> (V) at T <sub>J</sub> max. 650			
R <sub>DS(on)</sub> max. at 25 °C (Ω)	V <sub>GS</sub> = 10 V 0.340		
Q <sub>g</sub> (Max.) (nC) 90			
Q <sub>gs</sub> (nC)	14		
Q <sub>gd</sub> (nC) 22			
Configuration	Single		



#### **FEATURES**

- · Optimal Design
  - Low Area Specific On-Resistance
  - Low Input Capacitance (Ciss)
  - Reduced Capacitive Switching Losses
  - High Body Diode Ruggedness
  - Avalanche Energy Rated (UIS)
- Optimal Efficiency and Operation
  - Low Cost
  - Simple Gate Drive Circuitry
  - Low Figure-of-Merit (FOM):  $R_{on} \times Q_g$
  - Fast Switching
- Material categorization: For definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **APPLICATIONS**

- Consumer Electronics
  - Displays (LCD or Plasma TV)
- Lighting
- Industrial
  - Welding
  - Induction Heating
  - Motor Drives
  - Battery Chargers
- SMPS

ORDERING INFORMATION		
Package	TO-247AC	
Lead (Pb)-free	SiHG17N60D-E3	
Lead (Pb)-free and Halogen-free	SiHG17N60D-GE3	

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			$V_{DS}$	600	V
Gate-Source Voltage			$V_{GS}$	± 30	V
Continuous Proin Current /T = 150 °C)	V at 10 V	$T_{\rm C} = 25  ^{\circ}{\rm C}$ $T_{\rm C} = 100  ^{\circ}{\rm C}$		17	
Continuous Drain Current ( $T_J = 150 ^{\circ}\text{C}$ ) $V_{GS}$ at 10 V $T_C = 100 ^{\circ}\text{C}$		T <sub>C</sub> = 100 °C	l <sub>D</sub>	10.7	Α
Pulsed Drain Current <sup>a</sup>			I <sub>DM</sub>	48	
Linear Derating Factor				2.22	W/°C
Single Pulse Avalanche Energy <sup>b</sup>			E <sub>AS</sub>	165.6	mJ
Maximum Power Dissipation			$P_{D}$	277.8	W
Operating Junction and Storage Temperature Range			T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 150	°C
Drain-Source Voltage Slope T <sub>J</sub> = 125 °C		-1\	24	1//	
Reverse Diode dV/dt <sup>d</sup>		dV/dt	0.2	- V/ns	
Soldering Recommendations (Peak Temperature)c	for	10 s		300	°C

- a. Repetitive rating; pulse width limited by maximum junction temperature.
- b.  $V_{DD}$  = 50 V, starting  $T_J$  = 25 °C, L = 2.3 mH,  $R_g$  = 25  $\Omega$ ,  $I_{AS}$  = 12 A.
- c. 1.6 mm from case.
- d.  $I_{SD} \le I_D$ , starting  $T_J = 25$  °C.



# Vishay Siliconix

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.45	C/VV

PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static					•	I.	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0 V, I <sub>D</sub> = 250 μA	600	-	-	V
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	Referenc	e to 25 °C, I <sub>D</sub> = 1 mA	-	0.7	-	V/°C
Gate-Source Threshold Voltage (N)	V <sub>GS(th)</sub>	V <sub>DS</sub> :	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	3	-	5	V
Gate-Source Leakage	I <sub>GSS</sub>		V <sub>GS</sub> = ± 30 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		= 600 V, V <sub>GS</sub> = 0 V /, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	1	μA
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 8 A	-	0.275	0.340	Ω
Forward Transconductancea	9 <sub>fs</sub>	V <sub>DS</sub>	s = 50 V, I <sub>D</sub> = 8 A	-	6.2	-	S
Dynamic				L		L	
Input Capacitance	C <sub>iss</sub>		V <sub>GS</sub> = 0 V,	-	1780	-	
Output Capacitance	C <sub>oss</sub>		$V_{DS} = 100 V,$	-	140	-	рF
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1 MHz		-	15	-	
Total Gate Charge	$Q_g$			-	45	90	
Gate-Source Charge	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$I_D = 8 A, V_{DS} = 480 V$	-	14	-	nC
Gate-Drain Charge	Q <sub>gd</sub>			-	22	-	]
Turn-On Delay Time	t <sub>d(on)</sub>			-	22	45	
Rise Time	t <sub>r</sub>	$V_{\mathrm{DD}}$	= 300 V, I <sub>D</sub> = 8 A	-	56	85	ns
Turn-Off Delay Time	t <sub>d(off)</sub>	$R_g = 1$	9.1 $\Omega$ , $V_{GS} = 10 \text{ V}$	-	37	75	
Fall Time	t <sub>f</sub>			-	30	60	
Internal Gate Resistance	$R_g$	f = 1	MHz, open drain	-	1.6	-	Ω
<b>Drain-Source Body Diode Characteristic</b>	s						
Continuous Source-Drain Diode Current	I <sub>S</sub>	MOSFET sym showing the	bol	-	-	17	
Pulsed Diode Forward Current	I <sub>SM</sub>	integral reverse p - n junction diode		-	-	48	A
Body Diode Voltage	$V_{SD}$	$T_{\rm J} = 25^{\circ}$	$^{\circ}$ C, $I_{S} = 8$ A, $V_{GS} = 0$ V	-	-	1.5	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	_	25.20.1	-	633	950	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		= $25 ^{\circ}$ C, $I_F = I_S$ , 100 A/us, $V_D = 20 ^{\circ}$ V	-	7	15	μC
Reverse Recovery Current	I <sub>RRM</sub>	dl/dt = 100 A/ $\mu$ s, V <sub>R</sub> = 20 V		-	21	42	Α

### Note

a. Repetitive rating; pulse width limited by maximum junction temperature.



### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

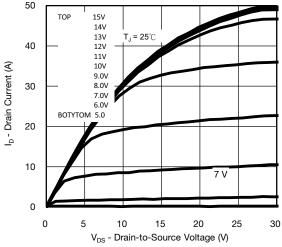


Fig. 1 - Typical Output Characteristics, T<sub>C</sub> = 150 °C

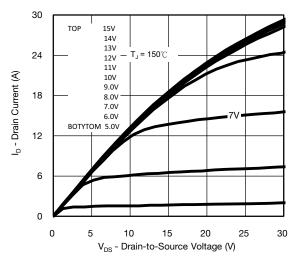


Fig. 2 - Typical Output Characteristics, T<sub>C</sub> = 150 °C

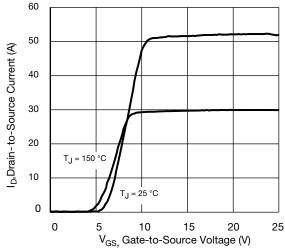


Fig. 3 - Typical Transfer Characteristics

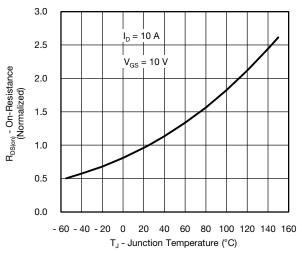


Fig. 4 - Normalized On-Resistance vs. Temperature

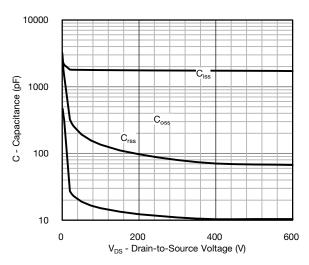


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

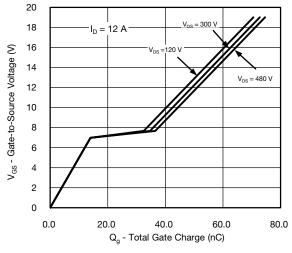


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



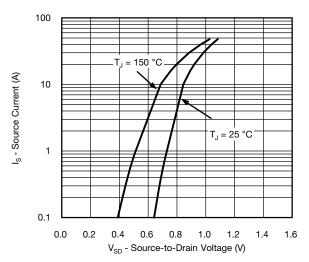


Fig. 7 - Typical Source-Drain Diode Forward Voltage

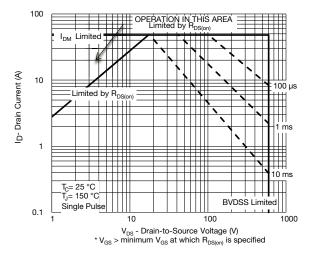


Fig. 8 - Maximum Safe Operating Area

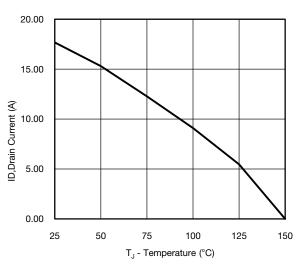


Fig. 9 - Maximum Drain Current vs. Case Temperature

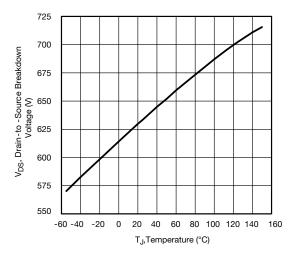


Fig. 10 - Typical Drain-to-Source Voltage vs. Temperature

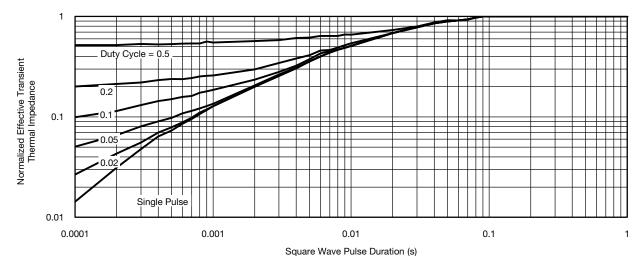


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

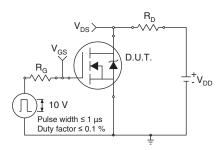


Fig. 12 - Switching Time Test Circuit

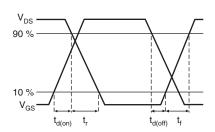


Fig. 13 - Switching Time Waveforms

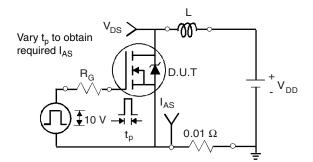


Fig. 14 - Unclamped Inductive Test Circuit

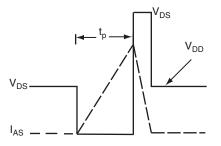


Fig. 15 - Unclamped Inductive Waveforms

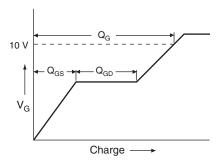


Fig. 16 - Basic Gate Charge Waveform

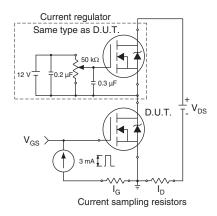
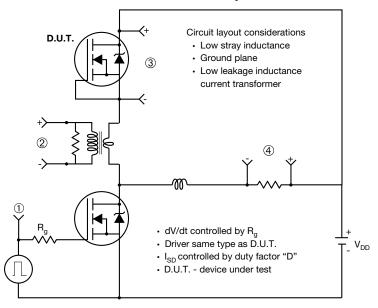


Fig. 17 - Gate Charge Test Circuit



#### Peak Diode Recovery dV/dt Test Circuit



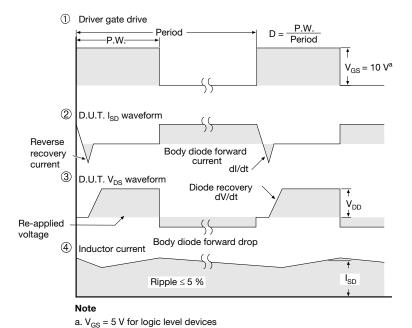


Fig. 18 - For N-Channel

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# **TO-247AC (High Voltage)**

#### **VERSION 1: FACILITY CODE = 9**







Section C--C,D--D,E--E

	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
Α	4.83	5.21	
A1	2.29	2.55	
A2	1.50	2.49	
b	1.12	1.33	
b1	1.12	1.28	
b2	1.91	2.39	6
b3	1.91	2.34	
b4	2.87	3.22	6, 8
b5	2.87	3.18	
С	0.55	0.69	6
c1	0.55	0.65	
D	20.40	20.70	4

	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
D1	16.25	16.85	5
D2	0.56	0.76	
E	15.50	15.87	4
E1	13.46	14.16	5
E2	4.52	5.49	3
е	5.44	BSC	
L	14.90	15.40	
L1	3.96	4.16	6
ØΡ	3.56	3.65	7
Ø P1	7.19 ref.		
Q	5.31	5.69	
S	5.54	5.74	

- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

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#### **VERSION 2: FACILITY CODE = Y**



	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
Α	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN		
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	254	
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

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### **VERSION 3: FACILITY CODE = N**



	MILLIM	IETERS
DIM.	MIN.	MAX.
Α	4.65	5.31
A1	2.21	2.59
A2	1.17	1.37
b	0.99	1.40
b1	0.99	1.35
b2	1.65	2.39
b3	1.65	2.34
b4	2.59	3.43
b5	2.59	3.38
С	0.38	0.89
c1	0.38	0.84
D	19.71	20.70
D1	13.08	-

	MILLIMETERS		
DIM.	MIN.	MAX.	
D2	0.51	1.35	
E	15.29	15.87	
E1	13.46	-	
е	5.46	BSC	
k	0.254		
L	14.20	16.10	
L1	3.71	4.29	
N	7.62	BSC	
Р	3.56	3.66	
P1	=	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

ECN: E20-0545-Rev. F, 19-Oct-2020

DWG: 5971

- <sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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